# 1 Characteristics

| Symbol                                 | Parameter  | Value                   | Unit                    |                            |                  |
|--|--|-------------------------|-------------------------|----------------------------|------------------|
| 1                                      |  |                         | T <sub>c</sub> = 108 °C | 16                         | А                |
| I <sub>T(RMS)</sub>                    | On-state rms current (full sine wave)  |                         | T <sub>c</sub> = 119 °C | 12                         | A                |
| 1                                      | Non repetitive surge peak on-state current (full                                   | F = 50 Hz               | t = 20 ms               | 120                        | А                |
| ITSM                                   |  | F = 60 Hz               | t = 16.7 ms             | 126                        | A                |
| l <sup>²</sup> t                       | I <sup>2</sup> t Value for fusing  |                         | t <sub>p</sub> = 10 ms  | 95                         | A <sup>2</sup> s |
| V <sub>DRM</sub> ,                     | Depetitive pack off state voltage, gate apen                                       | T <sub>j</sub> = 150 °C | 600                     | V                          |                  |
| V <sub>RRM</sub>                       | Repetitive peak off-state voltage, gate open                                       | T <sub>j</sub> = 125 °C | 800                     | v                          |                  |
| V <sub>DSM</sub> ,<br>V <sub>RSM</sub> | Non repetitive surge peak<br>off-state voltage $t_p = 10 \text{ ms}$               |                         | T <sub>j</sub> = 25 °C  | 900                        | V                |
| dl/dt                                  | Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ F = 100 Hz       |                         |                         |                            | A/µs             |
| I <sub>GM</sub>                        | Peak gate current $t_p = 20 \ \mu s$   |                         |                         | 4                          | А                |
| P <sub>G(AV)</sub>                     | Average gate power dissipation   |                         |                         | 1                          | W                |
| T <sub>stg</sub><br>T <sub>j</sub>     | Storage junction temperature range<br>Operating junction temperature range         |                         |                         | -40 to +150<br>-40 to +150 | °C               |
| TL                                     | Lead temperature for soldering during 10 s<br>(at 4 mm from case for TO220AB-ins.) |                         |                         | 260                        | °C               |
| V <sub>ins</sub> (rms)                 | Insulation rms voltage, 1 minute, TO220AB ceramic insulated                        |                         |                         | 2500                       | V                |

### Table 2. Absolute maximum rating (T<sub>i</sub> = 25 °C, unless otherwise specified)



| Table 5.                      | Electrical characteristics $(1_j = 25 \text{ C}, \text{ unless otherwise specified})$  |                         |          |         |       |      |
|-------------------------------|--|-------------------------|----------|---------|-------|------|
| Symbol                        | Test conditions  |                         | Quadrant |         | Value | Unit |
| ı (1)                         | $I_{GT}^{(1)}$ $V_{D} = 12 \text{ V}, \text{ R}_{L} = 30 \Omega$   |                         | -    -   | MIN.    | 0.5   | mA   |
| 'GT ` ′                       |  |                         | -    -   | MAX.    | 10    | mA   |
| V <sub>GT</sub>               | VD = 12 V, RL = 30 Ω   |                         | All      | MAX.    | 1.3   | V    |
| $V_{GD}$                      | $V_D = 800 \text{ V}, \text{ R}_L = 3.3 \text{ k}\Omega, \text{ T}_j = 125 ^\circ\text{C}$   |                         | All      | MIN.    | 0.2   | V    |
| I <sub>H</sub> <sup>(1)</sup> | I <sub>T</sub> = 500 mA  |                         |          | MAX.    | 25    | mA   |
| ۱L                            | 1 1.21   | -                       | MAX.     | 20      | mA    |      |
|                               | $I_{G} = 1.2 I_{GT}$   | Ш                       |          | 30      |       |      |
| dV/dt <sup>(1)</sup>          | $\label{eq:V_D} \begin{array}{ll} V_{D} = 67\% \ x \ 800 \ V \ gate \ open & T_{j} = 125 \ ^{\circ}\text{C} \\ \end{array} \\ \begin{array}{ll} V_{D} = 67\% \ x \ 600 \ V \ gate \ open & T_{j} = 150 \ ^{\circ}\text{C} \end{array}$ |                         |          | MIN.    | 100   | V/µs |
| uv/ul ()/                     |  |                         |          | IVIIIN. | 50    | v/µs |
|                               | (dV/dt)c = 0.1 V/µs  | T <sub>j</sub> = 125 °C |          |         | 9     |      |
| (dl/dt)c <sup>(1)</sup>       | (dV/dt)c = 10 V/µs   | T <sub>j</sub> = 125 °C |          | MIN.    | 3     | A/ms |
|                               | $(dV/dt)c = 0.1 V/\mu s 		 T_j = 150 \ ^{\circ}C$  |                         |          | WIIN.   | 5.4   | A/ms |
|                               | (dV/dt)c = 10 V/µs   | T <sub>j</sub> = 150 °C |          | 1       | 1.8   |      |
| t <sub>GT</sub>               | gate controlled turn on time I <sub>TM</sub> = 13 A, V <sub>D</sub> = 400 V, I <sub>G</sub> = 100 mA, dI <sub>G</sub> /dt = 100 mA/ $\mu$ s, R <sub>L</sub> = 30 $\Omega$  |                         | -    -   | TYP.    | 2     | μs   |

 Table 3.
 Electrical characteristics (T<sub>i</sub> = 25 °C, unless otherwise specified)

1. For both polarities of A2 referenced to A1

#### Table 4.Static characteristics

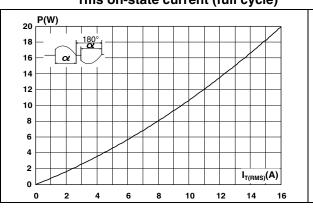
| Symbol                               | Test conditions                                   |                         |      | Value | Unit |
|--------------------------------------|---|-------------------------|------|-------|------|
| V <sub>TM</sub> <sup>(1)</sup>       | I <sub>TM</sub> = 22.6 A, t <sub>p</sub> = 380 μs | T <sub>j</sub> = 25 °C  | MAX. | 1.55  | V    |
| V <sub>to</sub> <sup>(1)</sup>       | Threshold voltage                                 | T <sub>j</sub> = 150 °C | MAX. | 0.85  | V    |
| R <sub>d</sub> <sup>(1)</sup>        | Dynamic resistance                                | T <sub>j</sub> = 150 °C | MAX. | 30    | mΩ   |
|                                      | V <sub>DRM</sub> = V <sub>RRM</sub> = 800 V       | T <sub>j</sub> = 25 °C  | MAX. | 5     | μA   |
| I <sub>DRM</sub><br>I <sub>RRM</sub> |   | T <sub>j</sub> = 125 °C |      | 1     | μ    |
|                                      | $V_{DRM} = V_{RRM} = 600 V$                       | T <sub>j</sub> = 150 °C |      | 3.6   | mA   |

1. for both polarities of A2 referenced to A1

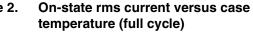
#### Table 5.Thermal resistance

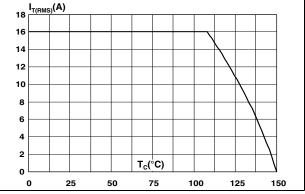
| Symbol               | Parameter             | Value | Unit |
|----------------------|-----------------------|-------|------|
| R <sub>th(j-c)</sub> | Junction to case (AC) | 2.1   | °C/W |
| R <sub>th(j-a)</sub> | Junction to ambient   | 60    | °C/W |





# Figure 1. Maximum power dissipation versus Figure 2. rms on-state current (full cycle)





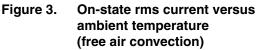
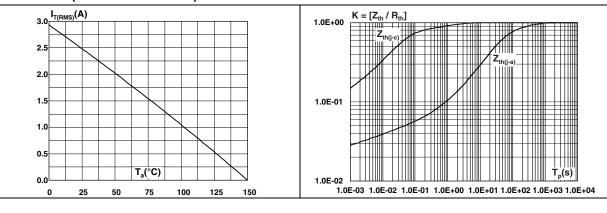


Figure 4. Relative variation of thermal impedance versus pulse duration



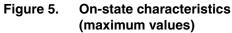
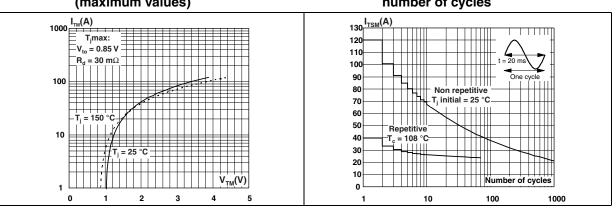
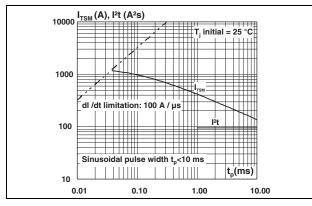


Figure 6. Surge peak on-state current versus number of cycles





# Figure 7. Non repetitive surge peak on-state Figure 8. current and corresponding values of I<sup>2</sup>t



# Figure 9. Relative variation of gate trigger voltage versus junction temperature (typical values)

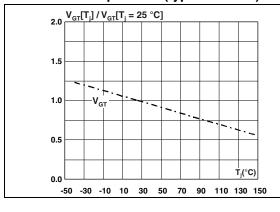
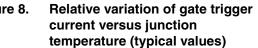


Figure 11. Relative variation of critical rate of Figure 12. decrease of current (dl/dt)c versus reapplied (dV/dt)c



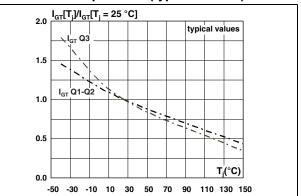
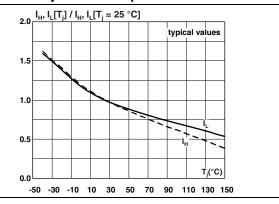
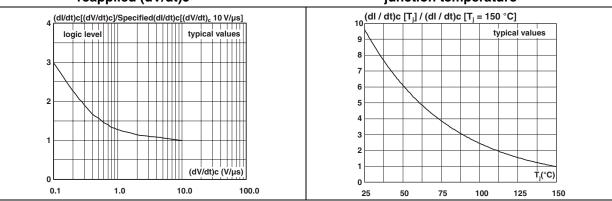


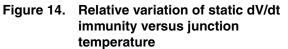
Figure 10. Relative variation of holding current and latching current versus junction temperature



Relative variation of critical rate of decrease of current (dl/dt)c versus junction temperature







T1610T-8I

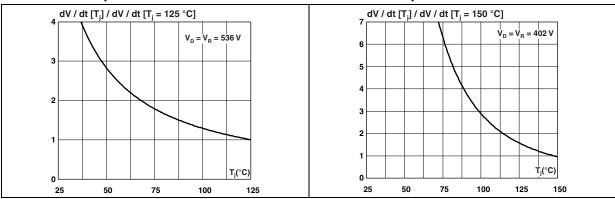
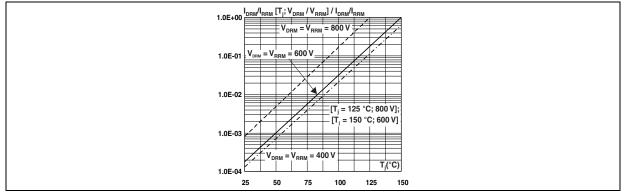


Figure 15. Relative variation of leakage current versus junction temperature for different values of blocking voltage





### 2 Package information

- Epoxy meets UL94, V0
- Recommended torque value: 0.4 to 0.6 N·m

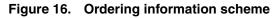
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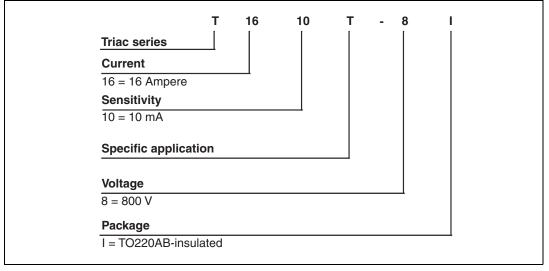
Table 6. TO-220AB insulated dimensions

|                              |             |    |       |             | Dimer | nsions |        |       |  |
|------------------------------|-------------|----|-------|-------------|-------|--------|--------|-------|--|
|                              |             |    |       | Millimeters |       |        | Inches |       |  |
|                              |             |    | Min.  | Тур.        | Max.  | Min.   | Тур.   | Max.  |  |
|                              |             | А  | 15.20 |             | 15.90 | 0.598  |        | 0.625 |  |
|                              |             | a1 |       | 3.75        |       |        | 0.147  |       |  |
| Ø I                          | C C         | a2 | 13.00 |             | 14.00 | 0.511  |        | 0.551 |  |
|                              | <u>b2</u> , | В  | 10.00 |             | 10.40 | 0.393  |        | 0.409 |  |
|                              | F           | b1 | 0.61  |             | 0.88  | 0.024  |        | 0.034 |  |
| A                            |             | b2 | 1.23  |             | 1.32  | 0.048  |        | 0.051 |  |
|                              |             | С  | 4.40  |             | 4.60  | 0.173  |        | 0.181 |  |
|                              | c2          | c1 | 0.49  |             | 0.70  | 0.019  |        | 0.027 |  |
|                              | <b>←→</b> _ | c2 | 2.40  |             | 2.72  | 0.094  |        | 0.107 |  |
|                              |             | е  | 2.40  |             | 2.70  | 0.094  |        | 0.106 |  |
|                              | M           | F  | 6.20  |             | 6.60  | 0.244  |        | 0.259 |  |
| <br>e <sup>→++</sup> •<br>b1 |             | ØI | 3.75  |             | 3.85  | 0.147  |        | 0.151 |  |
|                              |             | 14 | 15.80 | 16.40       | 16.80 | 0.622  | 0.646  | 0.661 |  |
|                              |             | L  | 2.65  |             | 2.95  | 0.104  |        | 0.116 |  |
|                              |             | 12 | 1.14  |             | 1.70  | 0.044  |        | 0.066 |  |
|                              |             | 13 | 1.14  |             | 1.70  | 0.044  |        | 0.066 |  |
|                              |             | М  |       | 2.60        |       |        | 0.102  |       |  |



# **3** Ordering information scheme







# 4 Ordering information

#### Table 7.Ordering information

| Order code | Marking   | Package               | Weight | Base qty | Delivery mode |
|------------|-----------|-----------------------|--------|----------|---------------|
| T1610T-8I  | T1610T-8I | TO-220AB<br>insulated | 2.3    | 50       | Tube          |

# 5 Revision history

#### Table 8.Document revision history

| Date        | Revision | Changes                                  |  |
|-------------|----------|--|--|
| 08-Aug-2011 | 1        | First issue.                             |  |
| 20-Jan-2012 | 2        | Corrected subscripting error in Table 3. |  |



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